

MOS INTEGRATED CIRCUIT μ PD78P4908

16-BIT SINGLE-CHIP MICROCONTROLLER

DESCRIPTION

The μ PD78P4908, 78K/IV series' product, is a one-time PROM version of the μ PD784907 and μ PD784908 with internal mask ROM.

Since user programs can be written to PROM, this microcomputer is best suited for evaluation in system development, manufacture of small quantities of multiple products, and fast start-up of applications.

For specific functions and other detailed information, consult the following user's manuals.

These manuals are required reading for design work.

 μ PD784908 Subseries User's Manual - Hardware : U11787E 78K/IV Series User's Manual - Instruction : U10905E

FEATURES

• 78K/IV series

Internal PROM: 128 KbytesInternal RAM: 4,352 bytes

Supply voltage: VDD = 4.5 to 5.5 V

(At main clock: fxx = 12.58 MHz, internal system clock = fxx: fcxx = 79 ns)

 $V_{DD} = 4.0 \text{ to } 5.5 \text{ V}$

(Other than above: fcyk = 159 ns)

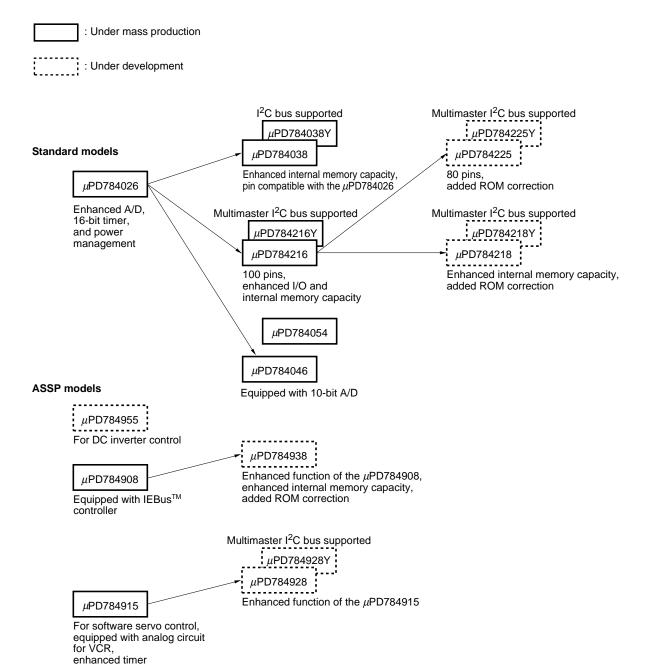
ORDERING INFORMATION

Part number		Package	Internal ROM	
μPD78P4	1908GF-3BA	100-pin plastic QFP (14 × 20 mm)	One-time PROM	

The information in this document is subject to change without notice.



* 78K/IV SERIES PRODUCT DEVELOPMENT DIAGRAM





FUNCTIONS

(1/2)

lte	em	Function				
Number of basic instructions (mnemonics)		113				
General-purpos	se register	8 bits × 16 registe	ers \times 8 banks, or 16 bits \times 8 regis	sters × 8 banks (memory mapping)		
Minimum instru	ction execution		1.27 µs/2.54 µs (at 6.29 MHz) 636 ns/1.27 µs (at 12.58 MHz)			
Internal	ROM	128 Kbytes				
memory	RAM	4,352 bytes				
Memory space		Program and data	a: 1 Mbyte			
I/O ports	Total	80				
	Input	8				
	Input/output	72				
Additional function	LED direct drive outputs	24				
pins ^{Note}	Transistor direct drive	8				
	N-ch open drain	4				
Real-time outpu	ut ports	4 bits \times 2, or 8 bits \times 1				
IEBus controlle	r	Incorporated (simple version)				
Timer/counter		Timer/counter 0: (16 bits)	Timer register \times 1 Capture register \times 1 Compare register \times 2	Pulse output capability Toggle output PWM/PPG output One-shot pulse output		
		Timer/counter 1: (16 bits)	Timer register × 1 Capture register × 1 Capture/compare register × 1 Compare register × 1	Real-time output port		
		Timer/counter 2: (16 bits)	Timer register × 1 Capture register × 1 Capture/compare register × 1 Compare register × 1	Pulse output capability Toggle output PWM/PPG output		
		Timer 3: (16 bits)	Timer register \times 1 Compare register \times 1			
Clock timer		Interrupt requests are generated at 0.5-second intervals. (A clock timer oscillator is incorporated.) Either the main clock (6.29 MHz/12.58 MHz) or real-time clock (32.768 kHz) can be selected as the input clock.				
Clock output		Selected from fclk, fclk/2, fclk/4, fclk/8, or fclk/16 (can be used as a 1-bit output port)				
PWM outputs		12-bit resolution × 2 channels				
Serial interface		UART/IOE (3-wire serial I/O) : 2 channels (incorporating baud rate generator) CSI (3-wire serial I/O) : 2 channels				

Note Additional function pins are included in the I/O pins.

*

(2/2)

Item		Function		
A/D converte	er	8-bit resolution × 8 channels		
Watchdog ti	mer	1 channel		
Standby		HALT/STOP/IDLE mode		
Interrupt	Hardware source	27 (20 internal, 7 external (sampling clock variable input: 1))		
	Software source	BRK or BRKCS instruction, operand error		
Nonmaskable		1 internal, 1 external		
Maskable		19 internal, 6 external		
		4-level programmable priority 3 operation statuses: vectored interrupt, macro service, context switching		
Power supply voltage		 V_{DD} = 4.5 to 5.5 V (At main clock: fxx = 12.58 MHz, internal system clock = fxx: fcγκ = 79 ns) V_{DD} = 4.0 to 5.5 V (Other than above: fcγκ = 159 ns) 		
Package		100-pin plastic QFP (14 × 20 mm)		



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1. DIFFERENCES BETWEEN μ PD78P4908 AND MASK ROM PRODUCTS

The μ PD78P4908 is produced by replacing the mask ROM in the μ PD784907 or μ PD784908 with PROM to which data can be written. The functions of the μ PD78P4908 are the same as those of the μ PD784907 or μ PD784908 except for the PROM specification such as writing and verification, except that the PROM size can be changed to 96 or 128 Kbytes, and except that the internal RAM size can be changed to 3,584 or 4,352 bytes.

Table 1-1 shows the differences between these products.

Table 1-1. Differences Between the μ PD78P4908 and Mask ROM Products

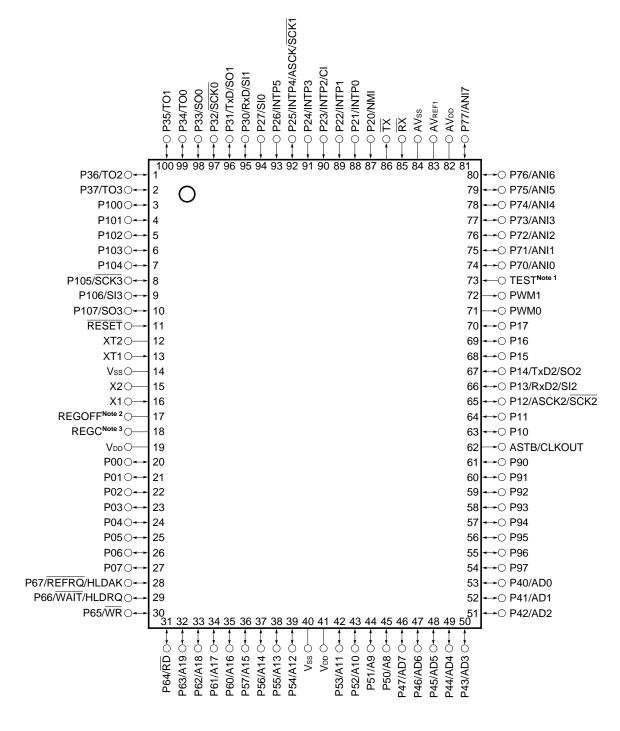
	Product name	μPD78P4908	μPD784907	μPD784908	
	Internal program memory • 128-Kbyte PROM • Can be changed to 96 Kbytes by IMS		96-Kbyte mask ROM	• 128-Kbyte mask ROM	
	Internal RAM • 4,352-byte internal RAM • Can be changed to 3,584 bytes by IMS		• 3,584-byte internal RAM	• 4,352-byte internal RAM	
	Pin connection	Pin functions related to writing or	reading of PROM have been adde	ed to the μ PD78P4908.	
*	Power supply voltage	 VDD = 4.5 to 5.5 V (At main clock: fxx = 12.58 MHz, internal system clock = fxx: fcγκ = 79 ns VDD = 4.0 to 5.5 V (Other than above: fcγκ = 159 ns) 	 V_{DD} = 4.0 to 5.5 V (At main clock: fxx = 12.58 MH fcγκ = 79 ns) V_{DD} = 3.5 to 5.5 V (Other than above: fcγκ = 159 	•	
	Electrical characteristics	Partially differs between these products.			



2. PIN CONFIGURATION (TOP VIEW)

(1) Normal operation mode

100-pin plastic QFP (14 × 20 mm)
 μPD78P4908GF-3BA



- Notes 1. Connect the TEST pin to Vss directly.
 - 2. Connect the REGOFF pin to Vss directly (select regulator operation)
 - 3. Connect the REGC pin to Vss through a 1- μ F capacitor.

μPD78P4908



A8-A19 : Address bus
AD0-AD7 : Address/data bus
ANI0-ANI7 : Analog input

ASCK, ASCK2: Asynchronous serial clock

ASTB : Address strobe AV_{DD} : Analog power supply AV_{REF1} : Reference voltage **AVss** : Analog ground CI : Clock input **CLKOUT** : Clock output **HLDAK** : Hold acknowledge **HLDRQ** : Hold request

INTP0-INTP5 : Interrupt from peripherals

NMI : Non-maskable interrupt

P00-P07 : Port 0 P10-P17 : Port 1 P20-P27 : Port 2 P30-P37 : Port 3 P40-P47 : Port 4 P50-P57 : Port 5 P60-P67 : Port 6 P70-P77 : Port 7 P90-P97 : Port 9 P100-P107 : Port 10 PWM0, PWM1: Pulse width modulation output

RD : Read strobe
REFRQ : Refresh request

REGC : Regulator capacitance

REGOFF : Regulator off

RESET : Reset

RX : IEBus receive data

RxD, RxD2 : Receive data

SCK0-SCK3 : Serial clock

SI0-SI3 : Serial input

SO0-SO3 : Serial output

TEST : Test

TO0-TO3 : Timer output

TX : IEBus transmit data

TxD, TxD2 : Transmit data

Vdd : Power supply

Vss : Ground

WAIT : Wait

WR : Write strobe

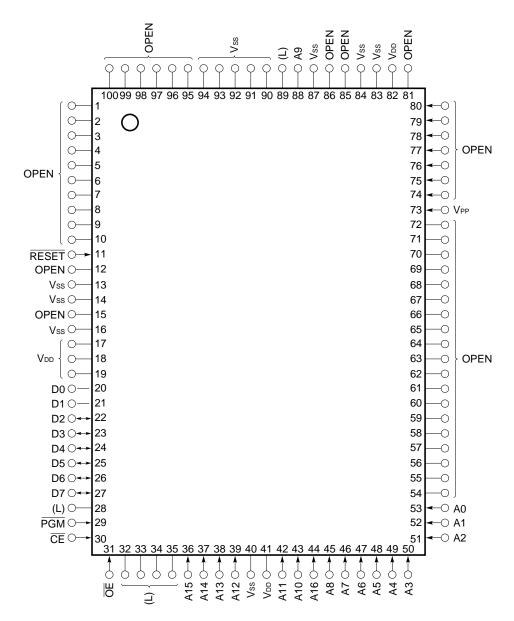
X1, X2 : Crystal (main system clock)

XT1, XT2 : Crystal (watch)



(2) PROM programming mode

• 100-pin plastic QFP (14 \times 20 mm) μ PD78P4908GF-3BA



Caution L : Connect these pins separately to the Vss pins through 10-k Ω pull-down resistors.

Vss : To be connected to the ground.

Open: Nothing should be connected on these pins.

RESET: Set a low-level input.

A0-A16 : Address bus RESET : Reset

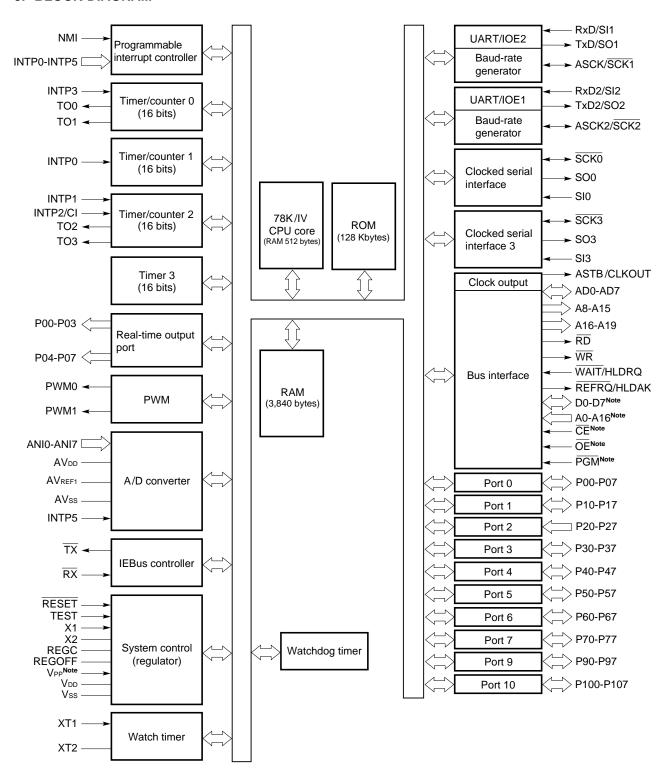
CE : Chip enable VDD : Power supply

D0-D7 : Data bus VPP : Programming power supply

PGM : Program



3. BLOCK DIAGRAM



Note In the PROM programming mode.



4. PIN FUNCTIONS

4.1 PINS FOR NORMAL OPERATING MODE

(1) Port pins (1/2)

Pin	I/O	Also used as	Function	
P00-P07	I/O	_	Port 0 (P0): • 8-bit I/O port. • Functions as a real-time output port (4 bits × 2). • Inputs and outputs can be specified bit by bit. • The use of built-in pull-up resistors can be simultaneously specified by software for all pins in input mode. • Can drive a transistor.	
P10	I/O	_	Port 1 (P1):	
P11		_	8-bit I/O port. Inputs and outputs can be specified bit by bit.	
P12		ASCK2/SCK2	The use of built-in pull-up resistors can be simultaneously specified by	
P13		RxD2/SI2	software for all pins in input mode.	
P14		TxD2/SO2	Can drive LED.	
P15-P17		_		
P20	Input	NMI	Port 2 (P2):	
P21		INTP0	8-bit input-only port. P20 does not function as a general-purpose port (nonmaskable interrupt). However, the input level can be checked by an interrupt service routine.	
P22		INTP1		
P23		INTP2/CI		
P24		INTP3	• The use of built-in pull-up resistors can be specified by software for pins	
P25		INTP4/ASCK/SCK1	P22 to P27 (in units of 6 bits). • The P25/INTP4/ASCK/SCK1 pin functions as the SCK1 input/output pin by CSIM1.	
P26		INTP5		
P27		SI0		
P30	I/O	RxD/SI1	Port 3 (P3):	
P31		TxD/SO1	• 8-bit I/O port.	
P32		SCK0	Inputs and outputs can be specified bit by bit. The use of built-in pull-up resistors can be simultaneously specified by	
P33		SO0	software for all pins in input mode.	
P34-P37		TO0-TO3	P32 and P33 can be set as the N-ch open-drain pin.	
P40-P47	I/O	AD0-AD7	Port 4 (P4): • 8-bit I/O port. • Inputs and outputs can be specified bit by bit. • The use of built-in pull-up resistors can be simultaneously specified by software for all pins in input mode. • Can drive LED.	

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(1) Port pins (2/2)

Pin	I/O	Also used as	Function	
P50-P57	I/O	A8-A15	Port 5 (P5): • 8-bit I/O port. • Inputs and outputs can be specified bit by bit. • The use of built-in pull-up resistors can be simultaneously specified by software for all pins in input mode. • Can drive LED.	
P60-P63	I/O	A16-A19	Port 6 (P6):	
P64		RD	8-bit I/O port.	
P65	7	WR	Inputs and outputs can be specified bit by bit. The use of built-in pull-up resistors can be simultaneously specified by	
P66		WAIT/HLDRQ	software for all pins in input mode.	
P67		REFRQ/HLDAK		
P70-P77	I/O	ANIO-ANI7	Port 7 (P7): • 8-bit I/O port. • Inputs and outputs can be specified bit by bit.	
P90-P97	I/O	_	Port 9 (P9): • 8-bit I/O port. • Inputs and outputs can be specified bit by bit. • The use of built-in pull-up resistors can be simultaneously specified by software for all pins in input mode.	
P100-P104	I/O	_	Port 10 (P10):	
P105	1	SCK3	• 8-bit I/O port.	
P106		SI3	Inputs and outputs can be specified bit by bit. The use of built-in pull-up resistors can be simultaneously specified by	
P107		SO3	software for all pins in input mode. • P105 and P107 can be set as the N-ch open-drain pin.	



(2) Non-port pins (1/2)

Pin	I/O	Also used as	Function	
TO0-TO3	Output	P34-P37	Timer output	
CI	Input	P23/INTP2	Input of a count clock for timer/counter 2	
RxD	Input	P30/SI1	Serial data input (UART0)	
RxD2		P13/SI2	Serial data input (UART2)	
TxD	Output	P31/SO1	Serial data output (UART0)
TxD2		P14/SO2	Serial data output (UART2	2)
ASCK	Input	P25/INTP4/SCK1	Baud rate clock input (UAF	RTO)
ASCK2		P12/SCK2	Baud rate clock input (UAF	RT2)
SI0	Input	P27	Serial data input (3-wire se	erial I/O 0)
SI1		P30/RxD	Serial data input (3-wire se	erial I/O 1)
SI2		P13/RxD2	Serial data input (3-wire se	erial I/O 2)
SI3		P106	Serial data input (3-wire se	erial I/O 3)
SO0	Output	P33	Serial data output (3-wire	serial I/O 0)
SO1		P31/TxD	Serial data output (3-wire	serial I/O 1)
SO2		P14/TxD2	Serial data output (3-wire	serial I/O 2)
SO3		P107	Serial data output (3-wire	serial I/O 3)
SCK0	I/O	P32	Serial clock I/O (3-wire ser	rial I/O 0)
SCK1		P25/INTP4/ASCK	Serial clock I/O (3-wire ser	rial I/O 1)
SCK2		P12/ASCK2	Serial clock I/O (3-wire ser	rial I/O 2)
SCK3		P105	Serial clock I/O (3-wire ser	rial I/O 3)
NMI	Input	P20	External interrupt request	_
INTP0		P21	-	Input of a count clock for timer/counter 1 Capture/trigger signal for CR11 or CR12
INTP1		P22		Input of a count clock for timer/counter 2 Capture/trigger signal for CR22
INTP2		P23/CI		Input of a count clock for timer/counter 2 Capture/trigger signal for CR21
INTP3		P24		Input of a count clock for timer/counter 0 Capture/trigger signal for CR02
INTP4		P25/ASCK/SCK1		_
INTP5		P26		Input of a conversion start trigger for A/D converter
AD0-AD7	I/O	P40-P47	Time multiplexing address,	/data bus (for connecting external memory)
A8-A15	Output	P50-P57	High-order address bus (fo	or connecting external memory)
A16-A19	Output	P60-P63	High-order address during address expansion (for connecting external memory	
RD	Output	P64	Strobe signal output for reading the contents of external memory	
WR	Output	P65	Strobe signal output for writing on external memory	
WAIT	Input	P66/HLDRQ	Wait signal insertion	
REFRQ	Output	P67/HLDAK	Refresh pulse output to ex	ternal pseudo static memory
HLDRQ	Input	P66/WAIT	Input of bus hold request	
HLDAK	Output	P67/REFRQ	Output of bus hold respons	se
ASTB	Output	CLKOUT	Latch timing output of time external memory)	e multiplexing address (A0-A7) (for connecting



(2) Non-port pins (2/2)

	Pin	I/O	Also used as	Function		
	CLKOUT	Output	ASTB	Clock output		
	PWM0	Output	_	PWM output 0		
	PWM1	Output	_	PWM output 1		
	RX	Input	_	Data input (IEBus)		
	TX	Output	_	Data output (IEBus)		
*	REGC	_	_	Capacitor connection for stabilizing the regulator output/Power supply when the regulator is stopped. Connect to Vss via a 1-μF capacitor.		
*	REGOFF	_	_	Signal for specifying regulator operation. Directly connect to Vss (regulator selected).		
	RESET	Input	_	Chip reset		
	X1	Input	_	Crystal input for system clock oscillation (A clock pulse can also be input		
	X2	_		to the X1 pin.)		
	XT1	Input	_	Real-time clock connection		
	XT2	_	_			
	ANI0-ANI7	Input	P70-P77	Analog voltage inputs for the A/D converter		
	AV _{REF1}	_	_	Application of A/D converter reference voltage		
	AV _{DD}			Positive power supply for the A/D converter		
	AVss			Ground for the A/D converter		
	V _{DD}			Positive power supply		
	Vss			Ground		
	TEST	Input		Directly connect to Vss. (The TEST pin is for the IC test.)		

4.2 PINS FOR PROM PROGRAMMING MODE ($V_{PP} \ge +5 \text{ V or } +12.5 \text{ V}, \overline{\text{RESET}} = L$)

4.2.1 Pin Functions

Pin name	I/O	Function			
VPP	_	PROM programming mode selection High voltage input during program write or verification			
RESET	Input	PROM programming mode selection			
A0-A16]	Address bus			
D0-D7	I/O	Data bus			
CE	Input	PROM enable input/program pulse input			
ŌĒ		Read strobe input to PROM			
PGM]	Program/program inhibit input during PROM programming mode			
V _{DD}	_	Positive power supply			
Vss	_	GND			



4.2.2 Pin Functions

(1) VPP (Programming power supply): Input

Input pin for setting the μ PD78P4908 to the PROM programming mode. When the input voltage on this pin is +6.5 V or more and when $\overline{\text{RESET}}$ input goes low, the μ PD78P4908 enters the PROM programming mode. When $\overline{\text{CE}}$ is made low for V_{PP} = +12.5 V and $\overline{\text{OE}}$ = high, program data on D0 to D7 can be written into the internal PROM cell selected by A0 to A16.

(2) RESET (Reset): Input

Input pin for setting the μ PD78P4908 to the PROM programming mode. When input on this pin is low, and when the input voltage on the V_{PP} pin goes +5 V or more, the μ PD78P4908 enters the PROM programming mode.

(3) A0 to A16 (Address bus): Input

Address bus that selects an internal PROM address (0000H to 1FFFFH)

(4) D0 to D7 (Data bus): I/O

Data bus through which a program is written on or read from internal PROM

(5) CE (Chip enable): Input

This pin inputs the enable signal from internal PROM. When this signal is active, a program can be written or read.

(6) OE (Output enable): Input

This pin inputs the read strobe signal to internal PROM. When this signal is made active for \overline{CE} = low, a one-byte program in the internal PROM cell selected by A0 to A16 can be read onto D0 to D7.

(7) PGM (Program): Input

The input pin for the operation mode control signal of the internal PROM.

Upon activation, writing to the internal PROM is enabled.

Upon inactivation, reading from the internal PROM is enabled.

(8) V_{DD}

Positive power supply pin

(9) Vss

Ground potential pin



4.3 I/O CIRCUITS FOR PINS AND HANDLING OF UNUSED PINS

Table 4-1 describes the types of I/O circuits for pins and the handling of unused pins.

Figure 4-1 shows the configuration of these various types of I/O circuits.

Table 4-1. Types of I/O Circuits for Pins and Handling of Unused Pins (1/2)

Pin	I/O circuit type	I/O	Recommended connection method for unused pins
P00-P07	5-A	I/O	Input state: To be connected to V _{DD}
P10, P11			Output state: To be left open
P12/ASCK2/SCK2	8-A		
P13/RxD2/SI2	5-A		
P14/TxD2/SO2			
P15-P17			
P20/NMI	2	Input	To be connected to V _{DD} or V _{SS}
P21/INTP0			
P22/INTP1	2-A	1	To be connected to V _{DD}
P23/INTP2/CI			
P24/INTP3			
P25/INTP4/ASCK/SCK1	8-A	I/O	Input state: To be connected to V _{DD} Output state: To be left open
P26/INTP5	2-A	Input	To be connected to V _{DD}
P27/SI0			
P30/RxD/SI1	5-A	I/O	Input state: To be connected to VDD
P31/TxD/SO1			Output state: To be left open
P32/SCK0	10-A		
P33/SO0			
P34/T00-P37/T03	5-A		
P40/AD0-P47/AD7			
P50/A8-P57/A15			
P60/A16-P63/A19			
P64/RD			
P65/WR			
P66/WAIT/HLDRQ			
P67/REFRQ/HLDAK			
P70/ANI0-P77/ANI7	20	I/O	Input state: To be connected to VDD or Vss
P90-P97	5-A		Output state: To be left open
P100-P104			
P105/SCK3	10-A		
P106/SI3	8-A		
P107/SO3	10-A]	
ASTB/CLKOUT	4	Output	To be left open



Table 4-1. Types of I/O Circuits for Pins and Handling of Unused Pins (2/2)

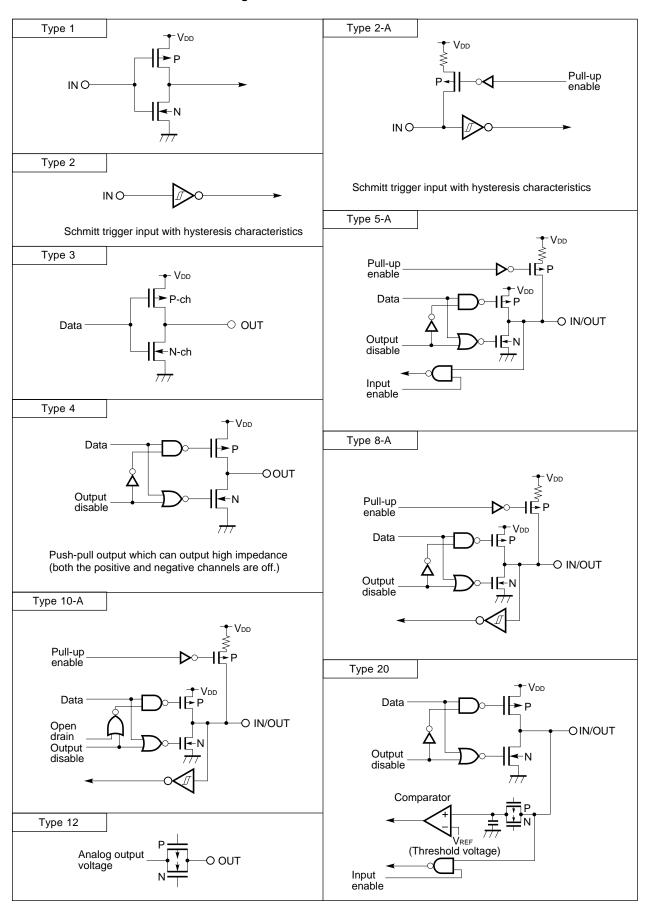
Pin	I/O circuit type	I/O	Recommended connection method for unused pins
RESET	2	Input	_
TEST	1		To be connected to Vss directly
XT2	_	_	To be left open
XT1		Input	To be connected to Vss
PWM0, PWM1	3	Output	To be left open
RX	1	Input	To be connected to V _{DD} or V _{SS}
TX	3	Output	To be left open
AV _{REF1}	_	_	To be connected to Vss
AVss			
AVDD			To be connected to V _{DD}

Caution When the I/O mode of an I/O dual-function pin is unpredictable, connect the pin to V_{DD} through a resistor of 10 to 100 k Ω (particularly when the voltage of the reset input pin becomes higher than that of the low level input at power-on or when I/O is switched by software).

Remark Since type numbers are consistent in the 78K series, those numbers are not always serial in each product. (Some circuits are not included.)



Figure 4-1. I/O Circuits for Pins





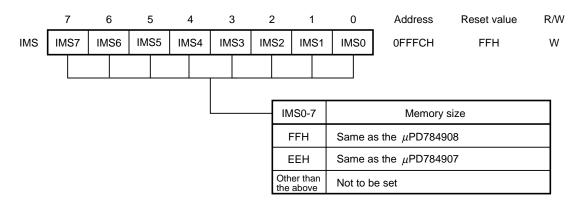
5. INTERNAL MEMORY SIZE SELECT REGISTER (IMS)

This register enables the software to avoid using part of the internal memory. The IMS can be set to establish the same memory mapping as used in mask ROM products that have different internal memory (ROM and RAM) configurations.

The IMS is set using 8-bit memory operation instructions.

A RESET input sets the IMS to FFH.

Figure 5-1. Internal Memory Size Select Register (IMS)



The IMS is not contained in a mask ROM product (μ PD784907 or μ PD784908). But the action is not affected if the write command to the IMS is executed to the mask ROM product.



6. PROM PROGRAMMING

The μ PD78P4908 has an on-chip 128-KB PROM device for use as program memory. When programming, set the VPP and $\overline{\text{RESET}}$ pins for PROM programming mode. See **2. PIN CONFIGURATION (TOP VIEW) (2) PROM programming mode** with regard to handling of other, unused pins.

6.1 OPERATION MODE

PROM programming mode is selected when +6.5 V is added to the V_{PD} pin, +12.5 V is added to the V_{PP} pin, or low-level input is added to the $\overline{\text{RESET}}$ pin. This mode can be set to operation mode by setting the $\overline{\text{CE}}$ pin, $\overline{\text{OE}}$ pin, and $\overline{\text{PGM}}$ pin as shown in Table 6-1 below.

In addition, the PROM contents can be read by setting read mode.

Table 6-1. PROM Programming Operation Mode

Pin	RESET	V _{PP}	V _{DD}	CE	ŌĒ	PGM	D0-D7
Operation mode							
Page data latch	L	+12.5 V	+6.5 V	Н	L	Н	Data input
Page write				н	н	L	High impedance
Byte write				L	Н	L	Data input
Program verify				L	L	Н	Data output
Program inhibit				×	Н	Н	High impedance
				×	L	L	
Read		+5 V	+5 V	L	L	Н	Data output
Output disable				L	Н	×	High impedance
Standby				Н	×	×	High impedance

Remark $\times = L$ or H



(1) Read mode

Set \overline{CE} to L and \overline{OE} to L to set read mode.

(2) Output disable mode

Set OE to H to set high impedance for data output and output disable mode.

Consequently, if several μ PD78P4908 devices are connected to a data bus, the \overline{OE} pins can be controlled to select data output from any of the devices.

(3) Standby mode

Set \overline{CE} to H to set standby mode.

In this mode, data output is set to high impedance regardless of the OE setting.

(4) Page data latch mode

At the beginning of page write mode, set \overline{CE} to H, \overline{PGM} to H, and \overline{OE} to L to set page data latch mode. In this mode, 1 page (4 bytes) of data are latched to the internal address/data latch circuit.

(5) Page write mode

After latching the address and data for one page (4 bytes) using page data latch mode, adding a 0.1 ms program pulse (active, low) to the \overline{PGM} pin with both \overline{CE} and \overline{OE} set to H causes page write to be executed. Later, setting both \overline{CE} and \overline{OE} to L causes program verification to be executed.

If programming is not completed after one program pulse, the write and verify operations may be repeated X times (where $X \le 10$).

(6) Byte write mode

Adding a 0.1 ms program pulse (active, low) to the PGM pin with setting \overline{CE} to L and \overline{OE} to H causes byte write to be executed. Later, setting \overline{OE} to L causes program verification to be executed.

If programming is not completed after one program pulse, the write and verify operations may be repeated X times (where $X \le 10$).

(7) Program verify mode

Set \overline{CE} to L, \overline{PGM} to H, and \overline{OE} to L to set program verify mode. Use verify mode for verification following each write operation.

(8) Program inhibit mode

Program inhibit mode is used to write to a single device when several μ PD78P4908 devices are connected in parallel to \overline{OE} , VPP, and D0 to D7 pins.

Use the page write mode or byte write mode described above for each write operation. Write operations cannot be done for devices in which the \overline{PGM} pin has been set to H.



6.2 PROM WRITE SEQUENCE

Start Address = G $V_{DD} = +6.5 \text{ V}, V_{PP} = +12.5 \text{ V}$ X = 0Latch Address = Address + 1 Latch Address = Address + 1 Latch Address = Address + 1 Address = Address + 1 Latch No X = X + 1Yes X = 10 ? 0.1 ms program pulse Fail Verify 4 bytes Pass Address = N? Yes $V_{DD} = 4.0$ to 5.5 V, $V_{PP} = V_{DD}$ Pass Fail Verify all bytes All pass Write end Defective

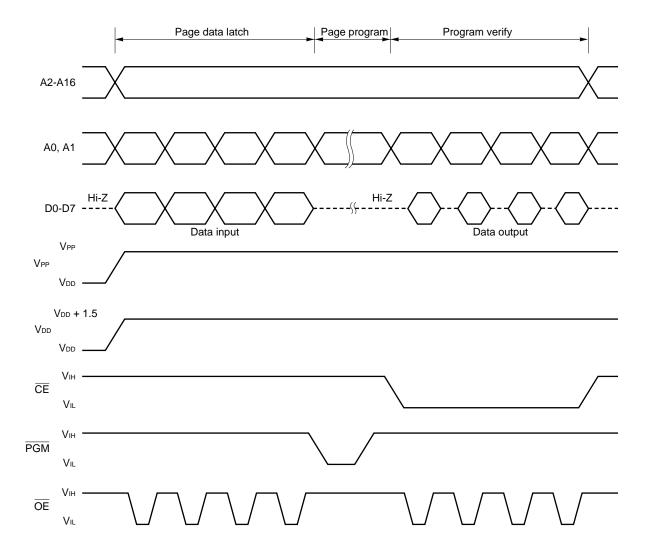
Figure 6-1. Page Program Mode Flowchart

Remark G = Start address

N = Program end address



Figure 6-2. Page Program Mode Timing



 μ PD78P4908



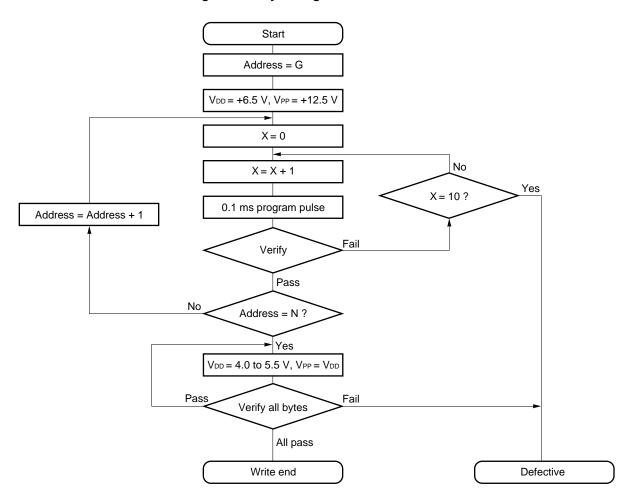


Figure 6-3. Byte Program Mode Flowchart

Remark G = Start address

N = Program end address

Program Program verify A0-A16 Hi-Z Hi-Z D0-D7 ---Data input Data output V_{PP} V_{PP} V_{DD} V_{DD} + 1.5 V_{DD} VDD - V_{IH} $\overline{\mathsf{CE}}$ V_{IL} V_{IH} PGM V_{IL} ŌĒ V_{IL}

Figure 6-4. Byte Program Mode Timing

Cautions 1. Add $V_{\mbox{\scriptsize DD}}$ before $V_{\mbox{\scriptsize PP}},$ and turn off the $V_{\mbox{\scriptsize DD}}$ after $V_{\mbox{\scriptsize PP}}.$

- 2. Do not allow $\ensuremath{V_{\text{PP}}}$ to exceed 13.5 V including overshoot.
- 3. Reliability problems may result if the device is inserted or pulled out while 12.5 V is applied at VPP.

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6.3 PROM READ SEQUENCE

Follow this sequence to read the PROM contents to an external data bus (D0 to D7).

- (1) Set the RESET pin to low level and add 5 V to the VPP pin. See 2. PIN CONFIGURATION (TOP VIEW) (2) PROM programming mode with regard to handling of other, unused pins.
- (2) Add 5 V to the VDD and VPP pins.
- (3) Input the data address to be read to pins A0 to A16.
- (4) Set read mode.
- (5) Output the data to pins D0 to D7.

Figure 6-5 shows the timing of steps (2) to (5) above.

Figure 6-5. PROM Read Timing

7. SCREENING ONE-TIME PROM PRODUCTS

NEC cannot execute a complete test of one-time PROM products (μ PD78P4908GF-3BA) due to their structure before shipment. It is recommended that you screen (verify) PROM products after writing necessary data into them and storing them at 125°C for 24 hours.



8. ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS (TA = 25 $^{\circ}$ C)

Parameter	Symbol	Conditions	Rating	Unit
Supply voltage	V _{DD}		-0.3 to +7.0	V
	AV _{DD}		-0.3 to V _{DD} + 0.3	V
	AVss		-0.3 to +0.3	V
Input voltage	VII	For pins other than VPP, A9	-0.3 to V _{DD} + 0.3	V
	V ₁₂	V _{PP} , A9	-0.3 to +13.5	V
Analog input voltage	Van		AVss - 0.3 to AVREF1 + 0.3	V
Output voltage	Vo		-0.3 to V _{DD} + 0.3	V
Output low current	loL	One pin	10	mA
		Total for the P00-P07, P30- P37, P54-P57, P60-P67, and P100-P107 pins	50	mA
		Total for the P10-P17, P40-P47, P50-P53, P70-P77, P90-P97, PWM0, PWM1, and $\overline{\text{TX}}$ pins	50	mA
Output high current	Іон	One pin	-6	mA
		Total for the P00-P07, P30- P37, P54-P57, P60-P67, and P100-P107 pins	-30	mA
		Total for the P10-P17, P40- P47, P50-P53, P70-P77, P90-P97, PWM0, PWM1, and TX pins	-30	mA
A/D converter reference input voltage	AVREF1		-0.3 to V _{DD} + 0.3	V
Operating ambient temperature	TA		-40 to +85	°C
Storage temperature	T _{stg}		-65 to +150	°C

Caution Absolute maximum ratings are rated values beyond which physical damage will be caused to the product; if the rated value of any of the parameters in the above table is exceeded, even momentarily, the quality of the product may deteriorate. Always use the product within its rated values.

Remark Unless otherwise stated, the characteristics of a dual-function pin are the same as those of a port pin.

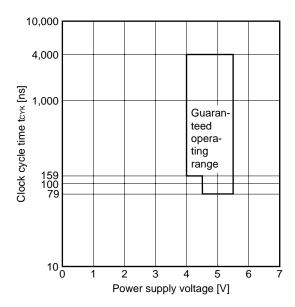
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OPERATING CONDITIONS

- Operating ambient temperature (T_A): -40 °C to +85 °C
- Power supply voltage and clock cycle time: See Figure 8-1.
- Internal regulator operation selected (REGOFF pin: low level)

Figure 8-1. Power Supply Voltage and Clock Cycle Time



CAPACITANCE (TA = 25 $^{\circ}$ C, VDD = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	Cı	f = 1 MHz			15	pF
Output capacitance	Со	0 V on pins other than measured pins			15	pF
I/O capacitance	Сю				15	pF



***** MAIN OSCILLATOR CHARACTERISTICS ($T_A = -40$ °C to +85 °C, $V_{DD} = 4.0$ to 5.5 V, $V_{SS} = 0$ V)

	Parameter	Symbol	Conditions	MIN.	MAX.	Unit
ſ	Oscillator frequency	fxx	Ceramic or crystal resonator	2	12.58	MHz

Caution When using the clock generator, run wires according to the following rules to avoid effects such as stray capacitance:

- Minimize the wiring length.
- · Never cause the wires to cross other signal lines.
- Never cause the wires to run near a line carrying a large varying current.
- The grounding point of the capacitor of the oscillator circuit must always be the same potential as Vss1. Never connect the capacitor to a ground pattern carrying a large current.
- · Never extract a signal from the oscillator.
- * Remark Connect a 12.582912 or 6.291456 MHz oscillator to operate the internal clock timer with the main clock.

CLOCK OSCILLATOR CHARACTERISTICS (Ta = -40 °C to +85 °C, V_{DD} = 4.0 to 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Oscillator frequency	fхт	Ceramic or crystal resonator	32	32.768	35	kHz
Oscillation settling time	tsxт	V _{DD} = 4.5 to 5.5 V		1.2	2	s
					10	S
Oscillation hold voltage	VDDXT		4.0		5.5	V
Watch timer operating voltage	VDDW		4.0		5.5	V



DC CHARACTERISTICS (T_A = -40 °C to +85 °C, V_{DD} = AV_{DD} = 4.0 to 5.5 V, V_{SS} = AV_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input low voltageNote 5	VIL1	For pins other than those described in Notes 1 and 2	-0.3		0.3 V _{DD}	V
	V _{IL2}	For pins described in Note 1	-0.3		0.2 V _{DD}	V
	VIL3	V _{DD} = 4.5 to 5.5 V For pins described in Note 2	-0.3		+0.8	V
Input high voltage	V _{IH1}	For pins other than those described in Notes 1 and 2	0.7 V _{DD}		V _{DD} + 0.3	V
	V _{IH2}	For pins described in Note 1	0.8 V _{DD}		V _{DD} + 0.3	V
	VIH3	V _{DD} = 4.5 to 5.5 V For pins described in Note 2	2.2		V _{DD} + 0.3	V
Output low voltage	V _{OL1}	IoL = 20 μA			0.1	V
		IoL = 100 μA			0.2	V
		IoL = 2 mA			0.4	V
	V _{OL2}	IoL = 8 mA For pins described in Note 4 VDD = 4.5 to 5.5 V			1.0	V
Output high voltage	V _{OH1}	Ioн = -20 μA	V _{DD} - 0.1			V
		Ιοн = -100 <i>μ</i> Α	V _{DD} - 0.2			V
		Iон = -2 mA	V _{DD} - 1.0			V
	V _{OH2}	V _{DD} = 4.5 to 5.5 V I _{OH} = -5 mA For pins described in Note 3	V _{DD} - 2.4			V

Notes 1. X1, X2, RESET, P12/ASCK2/SCK2, P20/NMI, P21/INTP0, P22/INTP1, P23/INTP2/CI, P24/INTP3, P25/INTP4/ASCK/SCK1, P26/INTP5, P27/SI0, P32/SCK0, P33/SO0, P105/SCK3, P106/SI3, P107/SO3, XT1, XT2

- **2.** P40/AD0-P47/AD7, P50/A8-P57/A15, P60/A16-P67/REFRQ/HLDAK, P00-P07
- **3.** P00-P07
- 4. P10-P17, P40/AD0-P47/AD7, P50/A8-P57/A15
- 5. Other than pull-up resistors



DC CHARACTERISTICS (TA = -40 °C to +85 °C, VDD = AVDD = 4.0 to 5.5 V, Vss = AVss = 0 V) (2/2)

Parameter	Symbol	Co	onditions	MIN.	TYP.	MAX.	Unit
Input leakage current	ILI1	$0 \text{ V} \leq V_I \leq V_{DD}$	For pins other than X1 and XT1			±10	μΑ
	I _{L12}		X1, XT1			±20	μΑ
Output leakage current	ILO	$0 \text{ V} \leq \text{V}_0 \leq \text{V}_{DD}$				±10	μΑ
V _{DD} supply currentNote	I _{DD1}	Operation mode	fxx = 12.58 MHz V _{DD} = 4.5 to 5.5 V		20	40	mA
			fxx = 6.29 MHz V _{DD} = 4.0 to 5.5 V		10	20	mA
loba	IDD2 HALT mode	HALT mode	fxx = 12.58 MHz VDD = 4.5 to 5.5 V fclk = fxx/8 (STBC = B1H) Peripheral operation stops.		5.2	10.4	mA
			fxx = 6.29 MHz VDD = 4.0 to 5.5 V fclk = fxx/8 (STBC = 31H) Peripheral operation stops.		2.6	5.2	mA
	IDD3	IDLE mode	fxx = 12.58 MHz V _{DD} = 4.5 to 5.5 V		2.4	4.8	mA
			fxx = 6.29 MHz V _{DD} = 4.0 to 5.5 V		1.8	3.6	mA
Pull-up resistor	RL	Vı = 0 V		15		80	kΩ

Note These values are valid when the internal regulator is ON (REGOFF pin = low level). They do not include the AV_{DD} and AV_{REF1} currents.



AC CHARACTERISTICS (TA = -40° C to $+85^{\circ}$ C, VDD = AVDD = 4.0 to 5.5 V, AVss = Vss = 0 V)

(1) Read/write operation

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Address setup time (to ASTB↓)	tsast	V _{DD} = 5.0 V	(0.5 + a)T – 11	29		ns
ASTB high-level width	twsтн	V _{DD} = 5.0 V	(0.5 + a)T – 17	23		ns
Address hold time (to ASTB↓)	t HSTLA	V _{DD} = 5.0 V	0.5T - 19	21		ns
Address hold time (to RD↑)	thra	V _{DD} = 5.0 V	0.5T - 14	26		ns
Delay from address to RD↓	tdar	V _{DD} = 5.0 V	(1 + a)T – 5	74		ns
Address float time (to RD↓)	t FRA			0		ns
Delay from address to data input	tdaid	VDD = 5.0 V	(2.5 + a + n)T - 37		400	ns
Delay from ASTB↓ to data input	tostio	V _{DD} = 5.0 V	(2 + n)T - 35		283	ns
Delay from RD↓ to data input	torio	V _{DD} = 5.0 V	(1.5 + n)T - 40		238	ns
Delay from ASTB↓ to RD↓	tostr	V _{DD} = 5.0 V	0.5T - 9	31		ns
Data hold time (to RD↑)	tHRID			0		ns
Delay from RD↑ to address active	tdra	V _{DD} = 5.0 V	0.5T – 2	38		ns
Delay from RD↑ to ASTB↑	t DRST	VDD = 5.0 V	0.5T - 9	31		ns
RD low-level width	twrL	V _{DD} = 5.0 V	(1.5 + n)T – 25	94		ns
Delay from address↓ to WR↓	t DAW	V _{DD} = 5.0 V	(1 + a)T – 5	74		ns
Address hold time (to WR↑)	thwa	V _{DD} = 5.0 V	0.5T - 14	26		ns
Delay from ASTB↓ to data output	tostod	V _{DD} = 5.0 V	0.5T + 15		55	ns
Delay from WR↓ to data output	towod				15	ns
Delay from ASTB↓ to WR↓	tostw	V _{DD} = 5.0 V	0.5T - 9	31		ns
Data setup time (to WR↑)	tsodwr	V _{DD} = 5.0 V	(1.5 + n)T – 20	99		ns
Data hold time (to WR↑)	thwod	V _{DD} = 5.0 V	0.5T - 14	26		ns
Delay from WR↑ to ASTB↑	towst	V _{DD} = 5.0 V	0.5T - 9	31		ns
WR low-level width	twwL	V _{DD} = 5.0 V	(1.5 + n)T - 25	94		ns

Remark T: t_{CYK} (system clock cycle time) $V_{DD} = 5.0 \text{ V}$ T = 79 ns (MIN.)

a: 1 during address wait, otherwise, 0

n: Number of wait states $(n \ge 0)$



(2) External wait timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Delay from address to WAIT↓ input	tdawt	V _{DD} = 5.0 V	(2 + a)T – 40		198	ns
Delay from ASTB↓ to WAIT↓ input	tоsтwт	VDD = 5.0 V	1.5T – 40		79	ns
Hold time from ASTB↓ to WAIT	tнsтwт	VDD = 5.0 V	(0.5 + n)T + 5	124		ns
Delay from ASTB↓ to WAIT↑	tostwth	VDD = 5.0 V	(1.5 + n)T - 40		238	ns
Delay from $\overline{RD} \!\!\downarrow to \; \overline{WAIT} \!\!\downarrow input$	tdrwtl	V _{DD} = 5.0 V	T – 40		39	ns
Hold time from RD↓ to WAIT	thrwt	VDD = 5.0 V	nT + 5	84		ns
Delay from RD↓ to WAIT↑	t DRWTH	VDD = 5.0 V	(1 + n)T - 40		198	ns
Delay from WAIT↑ to data input	towtid	VDD = 5.0 V	0.5T – 5		35	ns
Delay from WAIT↑ to RD↑	towtr	VDD = 5.0 V	0.5T	40		ns
Delay from WAIT↑ to WR↑	towtw	VDD = 5.0 V	0.5T	40		ns
Delay from WR↓ to WAIT↓ input	towwtl	VDD = 5.0 V	T – 40		39	ns
Hold time from WR↓ to WAIT	tнwwт	VDD = 5.0 V	nT + 5	84		ns
Delay from WR↓ to WAIT↑	t DWWTH	VDD = 5.0 V	(1 + n)T - 40		198	ns

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Remark T: t_{CYK} (system clock cycle time) $V_{DD} = 5.0 \text{ V}$ T = 79 ns (MIN.)

a: 1 during address wait, otherwise, 0

n: Number of wait states (n \geq 0)



(3) Bus hold timing

Parameter	Symbol	Conditions		MIN.	MAX.	Unit
Delay from HLDRQ↑ to float	trhac	VDD = 5.0 V	(2 + 4 + a + n)T + 50		765	ns
Delay from HLDRQ↑ to HLDAK↑	t dhqhhah	VDD = 5.0 V	(3 + 4 + a + n)T + 30		825	ns
Delay from float to HLDAK↑	t DCFHA	V _{DD} = 5.0 V	T + 30		109	ns
Delay from HLDRQ↓ to HLDAK↓	t DHQLHAL	VDD = 5.0 V	2T + 40		199	ns
Delay from HLDRQ↓ to active	t DHAC	V _{DD} = 5.0 V	T – 20	59		ns

Remark T: tcyk (system clock cycle time) VDD = 5.0 V T = 79 ns (MIN.)

a: 1 during address wait, otherwise, 0

n: Number of wait states (n \geq 0)

(4) Refresh timing

Parameter	Symbol	Conditions		MIN.	MAX.	Unit
Random read/write cycle time	trc	VDD = 5.0 V	ЗТ	238		ns
REFRQ low-level pulse width	twrfql	VDD = 5.0 V	1.5T – 25	94		ns
Delay from ASTB↓ to REFRQ	t DSTRFQ	VDD = 5.0 V	0.5T - 9	31		ns
Delay from RD↑ to REFRQ	t _{DRRFQ}	VDD = 5.0 V	1.5T – 9	110		ns
Delay from WR↑ to REFRQ	towrfq	VDD = 5.0 V	1.5T – 9	110		ns
Delay from REFRQ↑ to ASTB	t DRFQST	VDD = 5.0 V	0.5T - 9	31		ns
REFRQ high-level pulse width	twrfqh	VDD = 5.0 V	1.5T – 25	94		ns

Remark T: tcyk (system clock cycle time) Vdd = 5.0 V T = 79 ns (MIN.)



SERIAL OPERATION (Ta = -40 °C to +85 °C, Vdd = 4.0 to 5.5 V, AVss = Vss = 0 V)

(1) CSI, CSI3

Parameter	Symbol		Condition	S	MIN.	MAX.	Unit
Serial clock cycle time	tcysko	Input	fclk = fxx		8/fxx		ns
(SCKO, SCK3)			Other than fclk :	4/fclk		ns	
		Output	Other than fclk :	= fxx/8	8/fxx		ns
			fclk = fxx/8		16/fxx		ns
Serial clock low-level width	twsklo	Input	fclk = fxx		4/fxx - 40		ns
(SCK0, SCK3)			Other than fclk :	= fxx	2/fclк — 40		
		Output	Other than fclk :	= fxx/8	4/fxx - 40		μs
			fclk = fxx/8		8/fxx - 40		
Serial clock high-level width	twskH0	Input	fclk = fxx		4/fxx - 40		ns
(SCK0, SCK3)			Other than fclk = fxx		2/fclк — 40		
		Output Other than fclk = fxx/8		= fxx/8	4/fxx - 40		μs
			fclk = fxx/8		8/fxx - 40		
Setup time for SI0, SI3 (to SCK0, SCK3↑)	tsssko				80		ns
Hold time for SI0, SI3	thssk0	External	clock		1/fclk + 80		ns
(to SCK0, SCK3↑)		Internal	clock		80		
Output delay time for SO0,	tDSBSK1	CMOS p	oush-pull output	External clock	0	1/fclk + 150	ns
SO3 (to SCK0, SCK3↓)				Internal clock	0	150	ns
	tDSBSK2	Open-dr	ain output	External clock	0	1/fclk + 400	ns
		R∟ = 1 k	$R_L = 1 \text{ k}\Omega$ Internal clock		0	400	ns
Output hold time for SO0, SO3 (to SCK0, SCK3↑)	thsask	When d	ata is transferred		0.5tсүѕко – 40		ns

Remarks 1. The values in this table are those when fxx = 12.58 MHz, CL is 100 pF.

2. fclk: System clock frequency (selectable from fxx, fxx/2, fxx/4, and fxx/8 by the standby control register (STBC))

3. fxx : Oscillation frequency (fxx = 12.58 MHz or fxx = 6.29 MHz)



(2) IOE1, IOE2 (TA = -40 °C to +85 °C, VDD = AVDD = 4.0 to 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions		MIN.	MAX.	Unit
Serial clock cycle time (SCK1, SCK2)	tcysk1	Input	V _{DD} = 4.5 to 5.5 V	640		ns
				1,280		ns
		Output	Internal, divided by 8	Т		ns
Serial clock low-level width (SCK1, SCK2)	twskL1	Input	V _{DD} = 4.5 to 5.5 V	280		ns
				600		ns
		Output	Internal, divided by 8	0.5T - 40		ns
Serial clock high-level width (SCK1, SCK2)	twskH1	Input	V _{DD} = 4.5 to 5.5 V	280		ns
				600		ns
		Output	Internal, divided by 8	0.5T - 40		ns
Setup time for SI1 and SI2 (to SCK1, SCK2↑)	tsssк1			40		ns
Hold time for SI1 and SI2 (to SCK1, SCK2↑)	thssk1			40		ns
Output delay time for SO1 and SO2 (to SCK1, SCK2↓)	tososk			0	50	ns
Output hold time for SO1 and SO2 (to SCK1, SCK2↑)	thsosk	When da	ata is transferred	0.5tcүsк1 — 40		ns

Remarks 1. The values in this table are those when C_L is 100 pF.

2. T: Serial clock cycle set by software. The minimum value is 8/fxx.

(3) UART, UART2 (TA = -40 °C to +85 °C, VDD = AVDD = 4.0 to 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
ASCK clock input cycle time	tcyask	V _{DD} = 4.5 to 5.5 V	160		ns
			320		ns
ASCK clock low-level width	twaskl	V _{DD} = 4.5 to 5.5 V	65		ns
			120		ns
ASCK clock high-level width	twaskh	V _{DD} = 4.5 to 5.5 V	65		ns
			120		ns



CLOCK OUTPUT OPERATION (TA = -40° C to $+85^{\circ}$ C, VDD = AVDD = 4.0 to 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
CLKOUT cycle time	tcycL	nT	79	32,000	ns
CLKOUT low-level width	tcll	V _{DD} = 4.5 to 5.5 V, 0.5T – 10	30		ns
		0.5T – 20	20		ns
CLKOUT high-level width	tclh	V _{DD} = 4.5 to 5.5 V, 0.5T – 10	30		ns
		0.5T - 20	20		ns
CLKOUT rise time	tclr	4.5 V ≤ V _{DD} < 5.5 V		10	ns
		4.0 V ≤ V _{DD} < 4.5 V		20	ns
CLKOUT fall time	tclf	4.5 V ≤ V _{DD} < 5.5 V		10	ns
		4.0 V ≤ V _{DD} < 4.5 V		20	ns

Remark n: Dividing ratio set by software in the CPU (n = 1, 2, 4, 8, and 16)

T: tcyk (system clock cycle time)

OTHER OPERATIONS (TA = -40 $^{\circ}$ C to +85 $^{\circ}$ C, V_{DD} = AV_{DD} = 4.0 to 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
NMI low-level width	twnil		10		μs
NMI high-level width	twnih		10		μs
INTP0 low-level width	twitol		4 tcysmp		ns
INTP0 high-level width	twiтон		4 tсүзмр		ns
Low-level width for INTP1-INTP3 and CI	twiT1L		4 tсусри		ns
High-level width for INTP1-INTP3 and CI	twiT1H		4 tсүсри		ns
Low-level width for INTP4 and INTP5	twit2L		10		μs
High-level width for INTP4 and INTP5	t wiт2H		10		μs
RESET low-level widthNote	twrsL		10		μs
RESET high-level width	twrsh		10		μs

Note Use the RESET low-level width to ensure the lapse of the oscillation settling time when the power is applied.

Remark tcysmp: Sampling clock set by software

tcycpu: CPU operation clock set by software in the CPU



A/D CONVERTER CHARACTERISTICS (TA = -40 °C to +85 °C, VDD = AVDD = AVREF1 = 4.0 to 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Resolution				8			bit
Total errorNote		IEAD = 00H	FR = 0			0.6	%
			FR = 1			1.5	%
		IEAD = 01H	V _{DD} = 4.5 to 5.5 V		1	2.2	%
Quantization error						±1/2	LSB
Conversion time	tconv	FR = 1 120/fc	FR = 1 120/fclk			480	μs
		FR = 0 240/fc	ELK	19.1		960	μs
Sampling time	t SAMP	FR = 1 18/fcL	K	1.4		72	μs
		FR = 0 36/fcLi	K	2.9		144	μs
Analog input impedance	Ran				1,000		МΩ
AVREF1 impedance	R _{REF1}				10		kΩ
AV _{DD} power supply	Aldd1	CS = 1	CS = 1		2.0	5.0	mA
voltage	Aldd2	CS = 0, STOP	mode		1.0	20	μΑ

Note Quantization error is not included. This parameter is indicated as the ratio to the full-scale value.

Caution To execute the conversion by the A/D converter set port 7, multiplexed with the A/D input lines, to output mode to prevent data from being inverted.

Remark fclk: System clock frequency (selectable from fxx, fxx/2, fxx/4, and fxx/8 by the standby control register (STBC))

IEBUS CONTROLLER CHARACTERISTICS (Ta = -40°C to +85°C, VDD = AVDD = AVREF1 = 4.5 to 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
IEBus standard frequencyNote 1	fs	Transfer speed: mode 1	6.20	6.29	6.39	MHz
Driver delay time (delay from TX output to bus line)Note 2	t DTX	C _L = 50 pFNote 3			1.5	μs
Receiver delay time (delay from bus line to RX output)Note 2	torx				0.7	μs
Transmission delay on busNote 2	tobus				0.85	μs

Notes 1. The value conforms to the IEBus standard. The IEBus controller is operable within the range of the oscillator frequency of oscillator characteristics.

- **2.** The value is measured when IEBus system clock: fx = 6.29 MHz.
- **3.** C_L is the load capacitance of \overline{TX} output line.



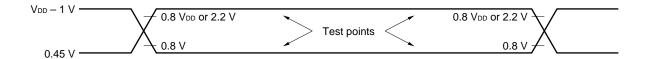
DATA RETENTION CHARACTERISTICS (T_A = -40 $^{\circ}$ C to +85 $^{\circ}$ C)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Data retention voltage	VDDDR	STOP mode		2.5		5.5	V
Data retention current	Idddr	STOP mode	VDDDR = 2.5 V, AVREF = 0 VNote 1		2	10	μΑ
			VDDDR = 4.0 to 5.5 V, AVREF1 = 0 VNote 1		10	50	μΑ
V _{DD} rise time	trvd			200			μs
V _{DD} fall time	t FVD			200			μs
V _{DD} hold time (to STOP mode setting)	t HVD			0			ms
STOP clear signal input time	t _{DREL}			0			ms
Oscillation settling time	twait	Crystal resor	nator	30			ms
		Ceramic resonator		5		0.1 VDDDR	ms
Input low voltage	VıL	Specific pinsNote 2		0		VDDDR	٧
Input high voltage	VIH			0.9 VDDDR			V

Notes 1. Valid when input voltages to the pins described in Note 2 satisfy V_{IL} or V_{IH} in the above table.

2. RESET, P12/ASCK2/SCK2, P20/NMI, P21/INTP0, P22/INTP1, P23/INTP2/CI, P24/INTP3, P25/INTP4/ASCK/SCK1, P26/INTP5, P27/SI0, P32/SCK0, P33/SO0, P105/SCK3, P106/SI3, and P107/SO3 pins

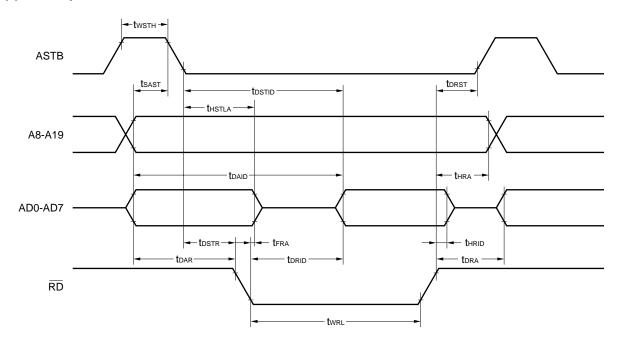
AC TIMING TEST POINTS



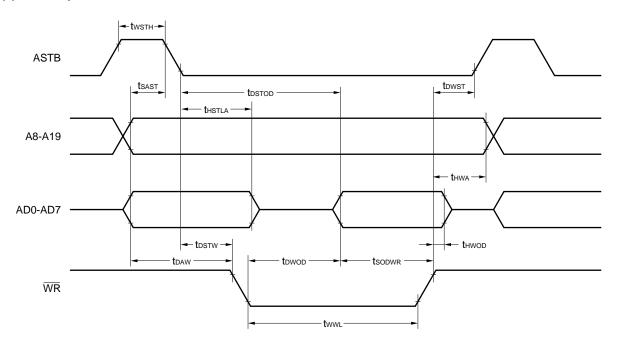


TIMING WAVEFORM

(1) Read operation

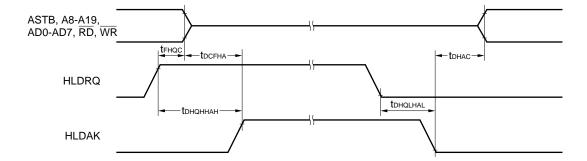


(2) Write operation



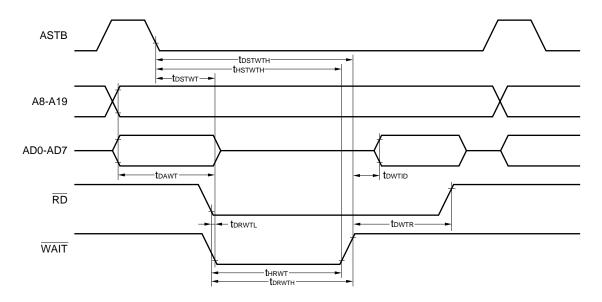


HOLD TIMING

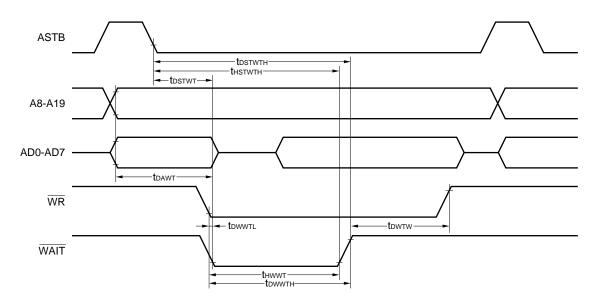


EXTERNAL WAIT SIGNAL INPUT TIMING

(1) Read operation



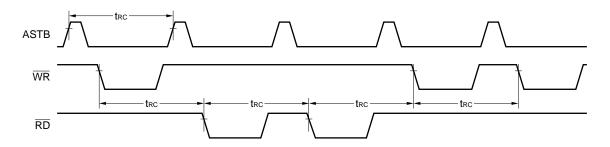
(2) Write operation



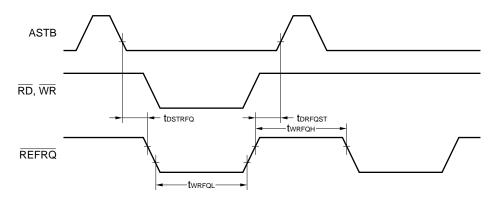


REFRESH TIMING WAVEFORM

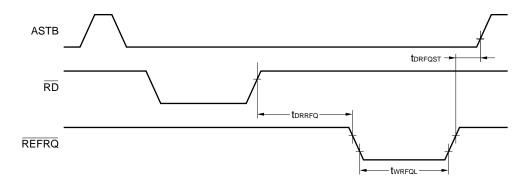
(1) Random read/write cycle



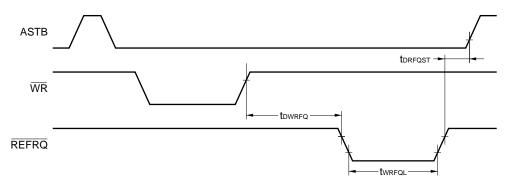
(2) When refresh memory is accessed for a read and write at the same time



(3) Refresh after a read

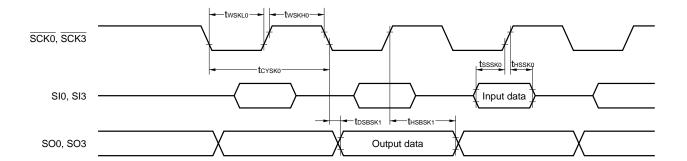


(4) Refresh after a write

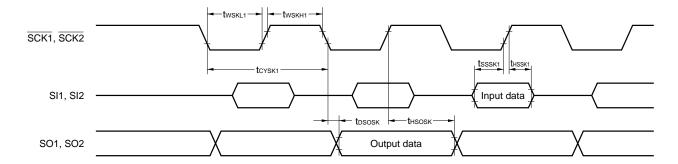




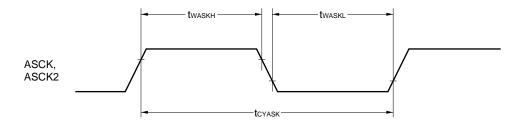
SERIAL OPERATION (CSI, CSI3)



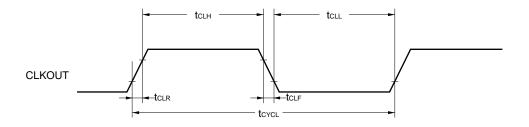
SERIAL OPERATION (IOE1, IOE2)



SERIAL OPERATION (UART, UART2)

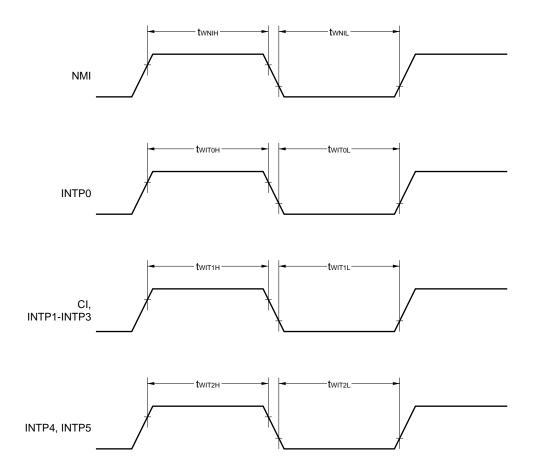


CLOCK OUTPUT TIMING

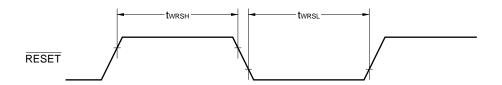




INTERRUPT REQUEST INPUT TIMING

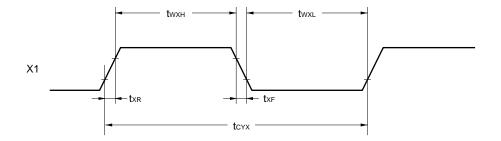


RESET INPUT TIMING

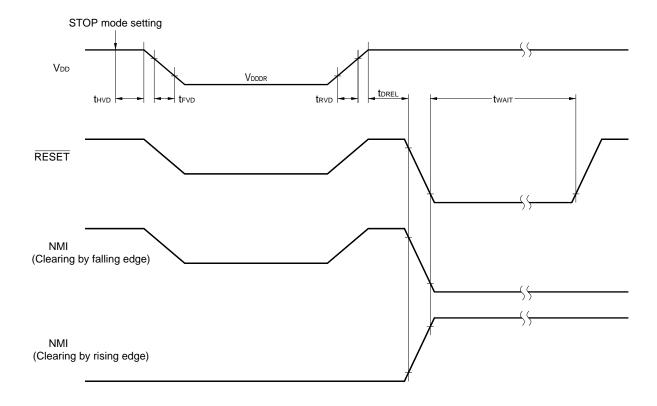




EXTERNAL CLOCK TIMING



DATA RETENTION CHARACTERISTICS





DC PROGRAMMING CHARACTERISTICS (TA = 25° C $\pm 5^{\circ}$ C, Vss = 0 V)

Parameter	Symbol	SymbolNote 1	Conditions	MIN.	TYP.	MAX.	Unit
High-level input voltage	Vін	Viн		2.2		V _{DDP} + 0.3	V
Low-level input voltage	VIL	VIL		-0.3		+0.8	V
Input leakage current	ILIP	lu	$0 \le V_1 \le V_{DDP}$ Note 2			±10	μΑ
High-level output voltage	Vон	Vон	Ioн = -400 μA	2.4			V
Low-level output voltage	Vol	Vol	IoL = 2.1 mA			0.45	V
Output leakage current	Ісо	-	$0 \le V_0 \le V_{DDP}, \overline{OE} = V_{IH}$			±10	μΑ
V _{DDP} supply voltage	V _{DDP}	Vcc	Program memory write mode	6.25	6.5	6.75	V
			Program memory read mode	4.5	5.0	5.5	V
V _{PP} supply voltage	V _{PP}	V _{PP}	Program memory write mode	12.2	12.5	12.8	V
			Program memory read mode		V _{PP} = V	DDP	V
VDDP supply current	IDD	IDD	Program memory write mode		10	40	mA
			Program memory read mode		10	40	mA
VPP supply current	IPP	IPP	Program memory write mode		5	50	mA
			Program memory read mode		1.0	100	μΑ

Notes 1. Symbols for the corresponding μ PD27C1001A

2. The V_{DDP} represents the V_{DD} pin as viewed in the programming mode.



AC PROGRAMMING CHARACTERISTICS (Ta = 25° C $\pm 5^{\circ}$ C, Vss = 0 V)

PROM Write Mode (Page Program Mode)

Parameter	Symbol ^{Note 1}	Conditions	MIN.	TYP.	MAX.	Unit
Address setup time	tas		2			μs
CE set time	tces		2			μs
Input data setup time	tos		2			μs
Address hold time	tан		2			μs
	t ahl		2			μs
	tahv		0			μs
Input data hold time	tон		2			μs
Output data hold time	tor		0		130	ns
V _{PP} setup time	tvps		2			μs
V _{DDP} setup time	t _{VDS} Note 2		2			μs
Initial program pulse width	t PW		0.095	0.1	0.105	ms
OE set time	toes		2			μs
Valid data delay time from OE	toe			1	2	ns
OE pulse width in the data latch	tıw		1			μs
PGM setup time	tрдмs		2			μs
CE hold time	tсен		2			μs
OE hold time	tоен		2			μs

Notes 1. These symbols (except typs) correspond to those of the corresponding μ PD27C1001A.

2. For μ PD27C1001A, read tvps as tvcs.



PROM Write Mode (Byte Program Mode)

Parameter	Symbol ^{Note} 1	Conditions	MIN.	TYP.	MAX.	Unit
Address setup time	tas		2			μs
CE set time	tces		2			μs
Input data setup time	tos		2			μs
Address hold time	tан		2			μs
Input data hold time	tон		2			μs
Output data hold time	t DF		0		130	ns
VPP setup time	tvps		2			μs
V _{DDP} setup time	t _{VDS} Note 2		2			μs
Initial program pulse width	tpw		0.095	0.1	0.105	ms
OE set time	toes		2			μs
Valid data delay time from OE	toe			1	2	ns

Notes 1. These symbols (except tvps) correspond to those of the corresponding μ PD27C1001A.

2. For μ PD27C1001A, read tvps as tvcs.

PROM Read Mode

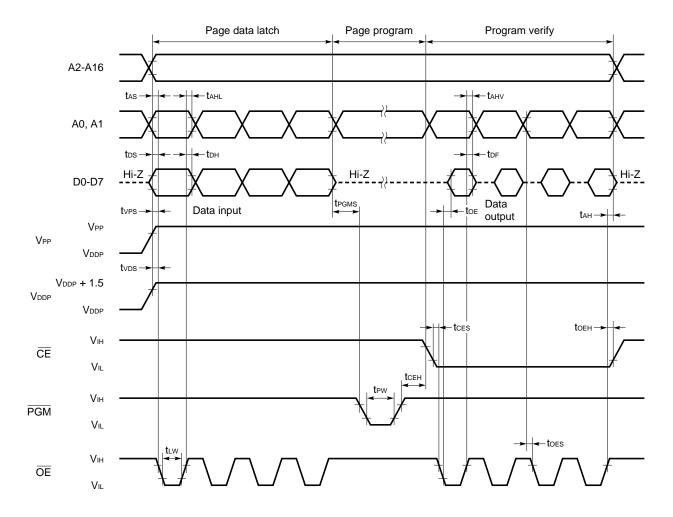
Parameter	SymbolNote 1	Conditions	MIN.	TYP.	MAX.	Unit
Data output time from address	tacc	CE = OE = VIL			200	ns
Delay from $\overline{CE}\ \downarrow$ to data output	t ce	OE = VIL		1	2	μs
Delay from $\overline{OE}\ \downarrow$ to data output	toe	CE = VIL		1	2	μs
Data hold time to OE↑ or CE↑Note 2	tor	CE = VIL or OE = VIL	0		60	ns
Data hold time to address	tон	CE = OE = VIL	0			ns

Notes 1. These symbols correspond to those of the corresponding μ PD27C1001A.

2. tdF is the time measured from when either \overline{OE} or \overline{CE} reaches ViH, whichever is faster.

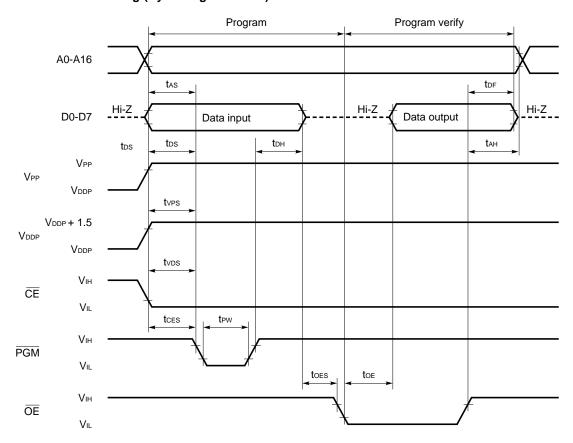


PROM Write Mode Timing (Page Program Mode)





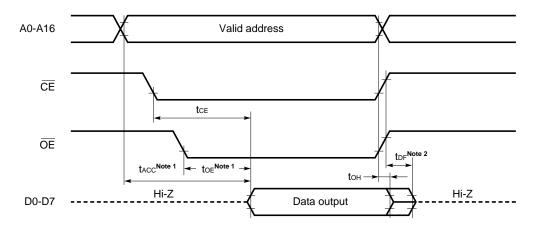
PROM Write Mode Timing (Byte Program Mode)



Cautions 1. VDDP must be applied before VPP, and must be cut after VPP.

- 2. VPP including overshoot must not exceed 13.5 V.
- 3. Plugging in or out the board with the VPP pin supplied with 12.5 V may adversely affect its reliability.

PROM Read Mode Timing



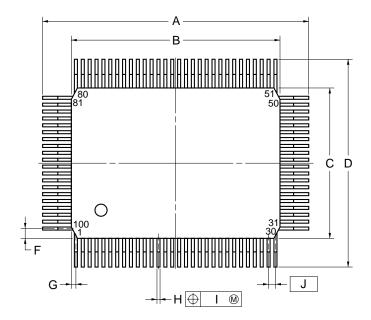
Notes 1. For reading within tacc, the delay of the \overline{OE} input from falling edge of \overline{CE} must be within tacc-toe.

2. tdF is the time measured from when either \overline{OE} or \overline{CE} reaches VIH, whichever is faster.

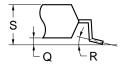


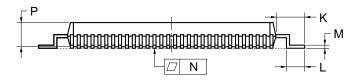
9. PACKAGE DRAWING

100PIN PLASTIC QFP (14x20)



detail of lead end





NOTE

Each lead centerline is located within 0.15 mm (0.006 inch) of its true position (T.P.) at maximum material condition.

Remark The shape and material of the ES version are the same as those of the corresponding mass-produced product.

ITEM	MILLIMETERS	INCHES
Α	23.6±0.4	0.929±0.016
В	20.0±0.2	$0.795^{+0.009}_{-0.008}$
С	14.0±0.2	$0.551^{+0.009}_{-0.008}$
D	17.6±0.4	0.693±0.016
F	0.8	0.031
G	0.6	0.024
Н	0.30±0.10	$0.012^{+0.004}_{-0.005}$
- 1	0.15	0.006
J	0.65 (T.P.)	0.026 (T.P.)
K	1.8±0.2	$0.071^{+0.008}_{-0.009}$
L	0.8±0.2	$0.031^{+0.009}_{-0.008}$
М	0.15 ^{+0.10} _{-0.05}	0.006+0.004
Ν	0.10	0.004
Р	2.7±0.1	$0.106^{+0.005}_{-0.004}$
Q	0.1±0.1	0.004±0.004
R	5°±5°	5°±5°
S	3.0 MAX.	0.119 MAX.

P100GF-65-3BA1-3



10. RECOMMENDED SOLDERING CONDITIONS

The conditions listed below shall be met when soldering the μ PD78P4908.

For details of the recommended soldering conditions, refer to our document **Semiconductor Device Mounting Technology Manual (C10535E)**.

Please consult with our sales offices in case any other soldering process is used, or in case soldering is done under different conditions.

Table 10-1. Soldering Conditions for Surface-Mount Devices

 μ PD78P4908GF-3BA: 100-pin plastic QFP (14 \times 20 mm)

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	Peak package's surface temperature: 235°C Reflow time: 30 seconds or less (210°C or more) Maximum allowable number of reflow processes: 2 Exposure limit: 7 daysNote (20 hours of pre-baking is required at 125°C afterward)	IR35-207-2
VPS	Peak package's surface temperature: 215°C Reflow time: 40 seconds or less (200°C or more) Maximum allowable number of reflow processes: 2 Exposure limit: 7 daysNote (20 hours of pre-baking is required at 125°C afterward)	VP15-207-2
Wave soldering	Solder temperature: 260°C or less Flow time: 10 seconds or less Number of flow processes: 1 Preheating temperature: 120°C MAX. (measured on the package surface) Exposure limit: 7 days Note (20 hours of pre-baking is required at 125°C afterward)	W\$60-207-1
Partial heating method	Terminal temperature: 300°C or less Heat time: 3 seconds or less (for one side of a device)	-

Note Maximum number of days during which the product can be stored at a temperature of 25°C and a relative humidity of 65% or less after dry-pack package is opened.

Caution Do not apply two or more different soldering methods to one chip (except for partial heating method for terminal sections).



APPENDIX A DEVELOPMENT TOOLS

The following development tools are available for system development using the μ PD78P4908. See also **(5) Notes on using development tools**.

(1) Language processing software

RA78K4	Assembler package for all 78K/IV series models
CC78K4	C compiler package for all 78K/IV series models
DF784908	Device file for μPD784908 subseries models
CC78K4-L	C compiler library source file for all 78K/IV series models

(2) PROM write tools

PG-1500	PROM programmer
PA-78P4908GF	Programmer adapter, connects to PG-1500
PG-1500 controller	Control program for PG-1500

(3) Debugging tools

• When using the in-circuit emulator IE-78K4-NS

IE-78K4-NS	In-circuit emulator for all 78K/IV series models
IE-70000-MC-PS-B	Power supply unit for IE-78K4-NS
IE-70000-98-IF-C	Interface adapter when the PC-9800 series computer (other than a notebook) is used as the host machine (C bus compatible)
IE-70000-CD-IF-A	PC card and interface cable when a notebook is used as the host machine (PCMCIA socket compatible)
IE-70000-PC-IF-C	Interface adapter when the IBM PC/AT TM compatible is used as the host machine (ISA compatible)
IE-7000-PCI-IF	Adapter when a computer with a PCI bus as the host machine
IE-784908-NS-EM1Note	Emulation board for evaluating μ PD784908 subseries models
NP-100GFNote	Emulation probe for 100-pin plastic QFP (GF-3BA type)
EV-9200GF-100	Socket for mounting on target system board made for 100-pin plastic QFP (GF-3BA type). Used in LCC mode.
ID78K4-NS	Integrated debugger for IE-78K4-NS
SM78K4	System simulator for all 78K/IV series models
DF784908	Device file for μ PD784908 subseries models

Note Under development

*



• When using the in-circuit emulator IE-784000-R

	IE-784000-R	In-circuit emulator for all 78K/IV series models
*	IE-70000-98-IF-C	Interface adapter when the PC-9800 series computer (other than a notebook) is used as the host machine (C bus compatible)
*	IE-70000-PC-IF-C	Interface adapter when the IBM PC/AT compatible is used as the host machine (ISA bus compatible)
*	IE-7000-PCI-IF	Adapter when a computer with a PCI bus as the host machine
	IE-78000-R-SV3	Interface adapter and cable when the EWS is used as the host machine
IE-784908-NS-EM1 Emulation board for evaluating μPD784908 substitution board for evaluating μPD784908 substit		Emulation board for evaluating μ PD784908 subseries models
	IE-784000-R-EM	Emulation board for all 78K/IV series models
	IE-78K4-R-EX2	Conversion board for emulation probes required to use the IE-784908-NS-EM1 on the IE-784000-R. The board is not needed when the conventional product IE-784908-R-EM1 is used.
	EP-78064-GF-R	Emulation probe for 100-pin plastic QFP (GF-3BA type)
	EV-9200GF-100	Socket for mounting on target system board made for 100-pin plastic QFP (GF-3BA type)
	ID78K4	Integrated debugger for IE-784000-R
SM78K4 System simulator for all 78K/IV series models		System simulator for all 78K/IV series models
DF784908 Device file for μPD784908 subseries models		Device file for μPD784908 subseries models

(4) Real-time OS

RX78K/IV	Real-time OS for 78K/IV series models
MX78K4	OS for 78K/IV series models



(5) Notes when using development tools

- The ID78K4-NS, ID78K4, and SM78K4 can be used in combination with the DF784908.
- The CC78K4 and RX78K/IV can be used in combination with the RA78K4 and DF784908.
- The NP-100GF is a product from Naito Densei Machida Mfg. Co., Ltd. (044-822-3813). Consult the NEC sales representative for purchasing.
- The host machines and operating systems corresponding to each software are shown below.

Host machine	PC	EWS
[OS]	PC-9800 series [Windows TM] IBM PC/AT compatibles [Windows]	HP9000 series 700 TM [HP-UX TM] SPARCstation TM [SunOS TM , Solaris TM] NEWS TM (RISC) [NEWS-OS TM]
RA78K4	Note	0
CC78K4	Note	0
PG-1500 controller	Note	-
ID78K4-NS	0	-
ID78K4	0	0
SM78K4	0	-
RX78K/IV	Note	0
MX78K4	Note	0

Note Software under MS-DOS

Data Sheet U11681EJ2V0DS00 55



APPENDIX B CONVERSION SOCKET (EV-9200GF-100) PACKAGE DRAWING

Connect the μ PD78P4908GF-3BA (100-pin plastic QFP (14 \times 20 mm)) to the circuit board in combination with the EV-9200GF-100.

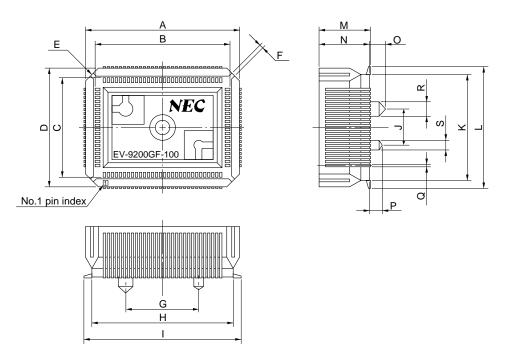
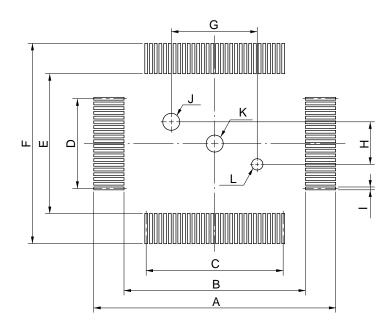


Figure B-1. Package Drawings of EV-9200GF-100 (Reference)

ITEM	MILLIMETERS	INCHES	
Α	24.6	0.969	
В	21	0.827	
С	15	0.591	
D	18.6	0.732	
Е	4-C 2	4-C 0.079	
F	0.8	0.031	
G	12.0	0.472	
Н	22.6	0.89	
I	25.3	0.996	
J	6.0	0.236	
K	16.6	0.654	
L	19.3	076	
М	8.2	0.323	
N	8.0	0.315	
0	2.5	0.098	
Р	2.0	0.079	
Q	0.35	0.014	
R	φ2.3	φ0.091	
S	φ1.5	φ0.059	



Figure B-2. Recommended Pattern to Mount EV-9200GF-100 on a Substrate (Reference)



EV-9200GF-100-P1E

ITEM	MILLIMETERS INCHES	
Α	26.3	1.035
В	21.6	0.85
С	$0.65\pm0.02\times29=18.85\pm0.05$	$0.026^{+0.001}_{-0.002} \times 1.142 = 0.742^{+0.002}_{-0.002}$
D	$0.65\pm0.02\times19=12.35\pm0.05$	$0.026^{+0.001}_{-0.002} \times 0.748 = 0.486^{+0.003}_{-0.002}$
E	15.6	0.614
F	20.3	0.799
G	12±0.05	$0.472^{+0.003}_{-0.002}$
Н	6±0.05	$0.236^{+0.003}_{-0.002}$
ı	0.35±0.02	$0.014^{+0.001}_{-0.001}$
J	φ2.36±0.03	ϕ 0.093 ^{+0.001} _{-0.002}
K	φ2.3	φ0.091
L	φ1.57±0.03	ϕ 0.062 ^{+0.001} _{-0.002}

Caution

Dimensions of mount pad for EV-9200 and that for target device (QFP) may be different in some parts. For the recommended mount pad dimensions for QFP, refer to "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (C10535E).



APPENDIX C RELATED DOCUMENTS

Documents Related to Devices

Document name		Document No.	
		Japanese	English
μPD784907, 784908 Data Sheet		U11680J	U11680E
μPD78P4908 Data Sheet		U11681J	This document
μPD784908 Subseries User's Manual – Hardware		U11787J	U11787E
μPD784908 Subseries Special Function Registers		U11589J	_
78K/IV Series User's Manual – Instruction		U10905J	U10905E
78K/IV Series Instruction Table		U10594J	_
78K/IV Series Instruction Set		U10595J	_
78K/IV Series Application Note Software Basic		U10095J	U10095E

Documents Related to Development Tools (User's Manual)

	Document name -		Document No.	
			Japanese	English
	RA78K4 Assembler Package	Operation	U11334J	U11334E
		Language	U11162J	U11162E
	RA78K Series Structured Assembler Preprocessor		U11743J	U11743E
	CC78K4 C Compiler	Operation	U11572J	U11572E
		Language	U11571J	U11571E
	PG-1500 PROM Programmer		U11940J	U11940E
	PG-1500 Controller PC-9800 Series (MS-DOS TM) Base		EEU-704	EEU-1291
	PG-1500 Controller IBM PC Series (PC DOSTM) Base		EEU-5008	U10540E
*	IE-78K4-NS		U13356J	U13356E
	IE-784000-R		U12903J	U12903E
	IE-784908-R-EM1		U11876J	_
*	IE-784908-NS-EM1		U13743J	On preparation
	EP-78064		EEU-934	EEU-1469
	SM78K4 System Simulator Windows Base	Reference	U10093J	U10093E
	SM78K Series System Simulator	External Part User Open Interface Specifications	U10092J	U10092E
	ID78K4-NS Integrated Debugger PC Base	Reference	U12796J	U12796E
	ID78K4 Integrated Debugger Windows Base	Reference	U10440J	U10440E
	ID78K4 Integrated Debugger HP-UX, SunOS, NEWS-OS Base	Reference	U11960J	U11960E

Caution The above documents may be revised without notice. Use the latest versions when you design application systems.



Documents Related to Software to Be Incorporated into the Product (User's Manual)

Document name		Document No.	
		Japanese	English
78K/IV Series Real-Time OS	Fundamental	U10603J	U10603E
	Installation	U10604J	U10604E
	Debugger	U10364J	_
OS for 78K/IV Series MX78K4	Fundamental	U11779J	_

Other Documents

Document name	Document No.	
Booting hame	Japanese	English
NEC IC Package Manual (CD-ROM)	_	C13388E
Semiconductor Device Mounting Technology Manual	C10535J	C10535E
Quality Grades on NEC Semiconductor Device	C11531J	C11531E
NEC Semiconductor Device Reliability/Quality Control System	C10983J	C10983E
Guide to Prevent Damage for Semiconductor Devices by Electrostatic Discharge (ESD)	C11892J	C11892E
Guide to Quality Assurance for Semiconductor Devices	_	MEI-1202
Guide for Products Related to Microcomputer: Other Companies	U11416J	_

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NOTES FOR CMOS DEVICES -

(1) PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS device behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.



Regional Information

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- · Device availability
- Ordering information
- · Product release schedule
- · Availability of related technical literature
- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)
- · Network requirements

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Anti-radioactive design is not implemented in this product.

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